

Trench gate field-stop IGBT M series, 650 V, 15 A low-loss in a TO-220FP package

Datasheet - production data

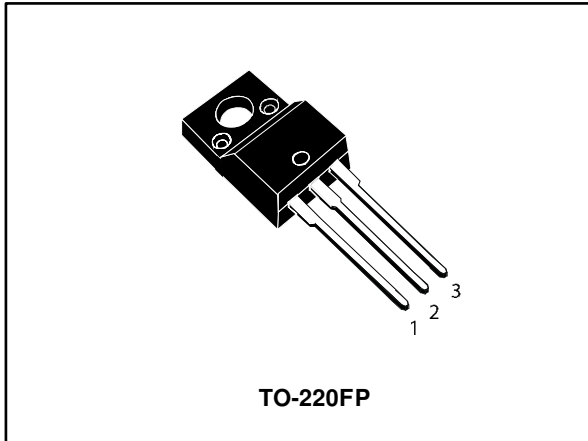
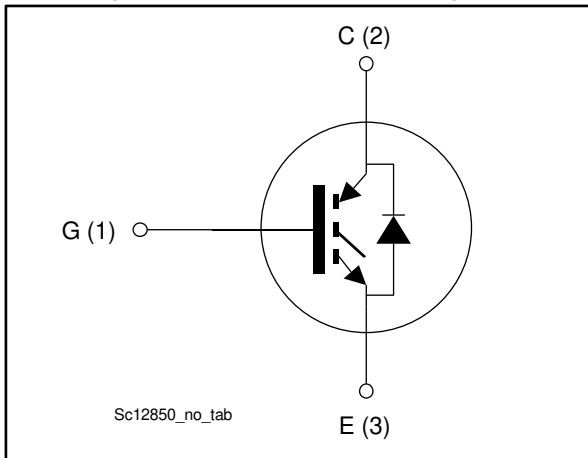


Figure 1: Internal schematic diagram



Features

- 6 μ s of short-circuit withstand time
- $V_{CE(sat)} = 1.55$ V (typ.) @ $I_C = 15$ A
- Tight parameter distribution
- Safer paralleling
- Positive $V_{CE(sat)}$ temperature coefficient
- Low thermal resistance
- Soft and very fast recovery antiparallel diode
- Maximum junction temperature: $T_J = 175$ °C

Applications

- Motor control
- UPS
- PFC
- General purpose inverter

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the M series IGBTs, which represent an optimal balance between inverter system performance and efficiency where low-loss and short-circuit functionality are essential. Furthermore, the positive $V_{CE(sat)}$ temperature coefficient and tight parameter distribution result in safer paralleling operation.

Table 1: Device summary

Order code	Marking	Package	Packing
STGF15M65DF2	G15M65DF2	TO-220FP	Tube

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{GE} = 0 V)	650	V
I _C ⁽¹⁾	Continuous collector current at T _C = 25 °C	30	A
I _C ⁽¹⁾	Continuous collector current at T _C = 100 °C	15	A
I _{CP} ⁽²⁾	Pulsed collector current	60	A
V _{GE}	Gate-emitter voltage	±20	V
I _F ⁽¹⁾	Continuous forward current at T _C = 25 °C	30	A
I _F ⁽¹⁾	Continuous forward current at T _C = 100 °C	15	A
I _{FP} ⁽²⁾	Pulsed forward current	60	A
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T _C = 25 °C)	2.5	kV
P _{TOT}	Total dissipation at T _C = 25 °C	31	W
T _{STG}	Storage temperature range	- 55 to 150	°C
T _J	Operating junction temperature range	- 55 to 175	°C

Notes:

⁽¹⁾Limited by maximum junction temperature.

⁽²⁾Pulse width limited by maximum junction temperature.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
R _{thJC}	Thermal resistance junction-case IGBT	4.8	°C/W
R _{thJC}	Thermal resistance junction-case diode	6.25	°C/W
R _{thJA}	Thermal resistance junction-ambient	62.5	°C/W

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 4: Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$, $I_C = 250\text{ }\mu\text{A}$	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 15\text{ A}$		1.55	2.0	V
		$V_{GE} = 15\text{ V}$, $I_C = 15\text{ A}$, $T_J = 125\text{ °C}$		1.9		
		$V_{GE} = 15\text{ V}$, $I_C = 15\text{ A}$, $T_J = 175\text{ °C}$		2.1		
V_F	Forward on-voltage	$I_F = 15\text{ A}$		1.7	2.6	V
		$I_F = 15\text{ A}$, $T_J = 125\text{ °C}$		1.5		
		$I_F = 15\text{ A}$, $T_J = 175\text{ °C}$		1.4		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 500\text{ }\mu\text{A}$	5	6	7	V
I_{CES}	Collector cut-off current	$V_{GE} = 0\text{ V}$, $V_{CE} = 650\text{ V}$			25	μA
I_{GES}	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			± 250	μA

Table 5: Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0\text{ V}$	-	1250	-	pF
C_{oes}	Output capacitance		-	80	-	
C_{res}	Reverse transfer capacitance		-	25	-	
Q_g	Total gate charge	$V_{CC} = 520\text{ V}$, $I_C = 15\text{ A}$, $V_{GE} = 0\text{ to }15\text{ V}$ (see Figure 30: "Gate charge test circuit")	-	45	-	nC
Q_{ge}	Gate-emitter charge		-	11	-	
Q_{gc}	Gate-collector charge		-	15	-	

Table 6: IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 15\text{ A}$, $V_{GE} = 15\text{ V}$, $R_G = 12\ \Omega$ (see Figure 29: "Test circuit for inductive load switching")	-	24	-	ns
t_r	Current rise time		-	7.8	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1570	-	A/ μ s
$t_{d(off)}$	Turn-off-delay time		-	93	-	ns
t_f	Current fall time		-	106	-	ns
$E_{on}^{(1)}$	Turn-on switching energy		-	0.09	-	mJ
$E_{off}^{(2)}$	Turn-off switching energy		-	0.45	-	mJ
E_{ts}	Total switching energy		-	0.54	-	mJ
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 15\text{ A}$, $V_{GE} = 15\text{ V}$, $R_G = 12\ \Omega$ $T_J = 175\text{ }^\circ\text{C}$ (see Figure 29: "Test circuit for inductive load switching")	-	24.8	-	ns
t_r	Current rise time		-	9.2	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1300	-	A/ μ s
$t_{d(off)}$	Turn-off-delay time		-	96	-	ns
t_f	Current fall time		-	169	-	ns
$E_{on}^{(1)}$	Turn-on switching energy		-	0.22	-	mJ
$E_{off}^{(2)}$	Turn-off switching energy		-	0.61	-	mJ
E_{ts}	Total switching energy		-	0.83	-	mJ
t_{sc}	Short-circuit withstand time	$V_{CC} \leq 400\text{ V}$, $V_{GE} = 15\text{ V}$, $T_{Jstart} = 150\text{ }^\circ\text{C}$	6		-	μ s
		$V_{CC} \leq 400\text{ V}$, $V_{GE} = 13\text{ V}$, $T_{Jstart} = 150\text{ }^\circ\text{C}$	10			

Notes:

(1)Including the reverse recovery of the diode.

(2)Including the tail of the collector current.

Table 7: Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 15\text{ A}$, $V_R = 400\text{ V}$, $V_{GE} = 15\text{ V}$, $di/dt = 1000\text{ A}/\mu\text{s}$ (see Figure 29: "Test circuit for inductive load switching")	-	142		ns
Q_{rr}	Reverse recovery charge		-	525		nC
I_{rrm}	Reverse recovery current		-	13.4		A
dl_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	790		A/ μ s
E_{rr}	Reverse recovery energy		-	64		μ J
t_{rr}	Reverse recovery time	$I_F = 15\text{ A}$, $V_R = 400\text{ V}$, $V_{GE} = 15\text{ V}$, $di/dt = 1000\text{ A}/\mu\text{s}$, $T_J = 175\text{ }^\circ\text{C}$ (see Figure 29: "Test circuit for inductive load switching")	-	241		ns
Q_{rr}	Reverse recovery charge		-	1690		nC
I_{rrm}	Reverse recovery current		-	20		A
dl_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	420		A/ μ s
E_{rr}	Reverse recovery energy		-	176		μ J

2.1 Electrical characteristics (curves)

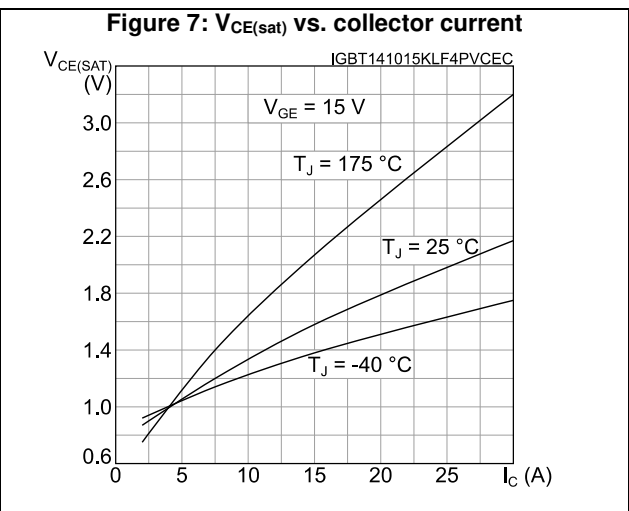
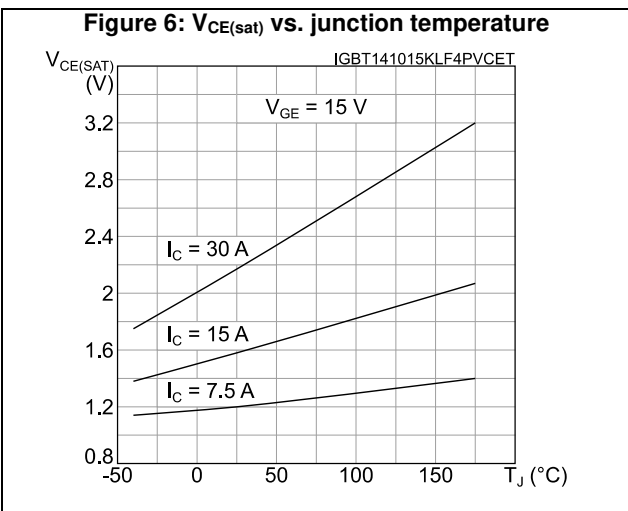
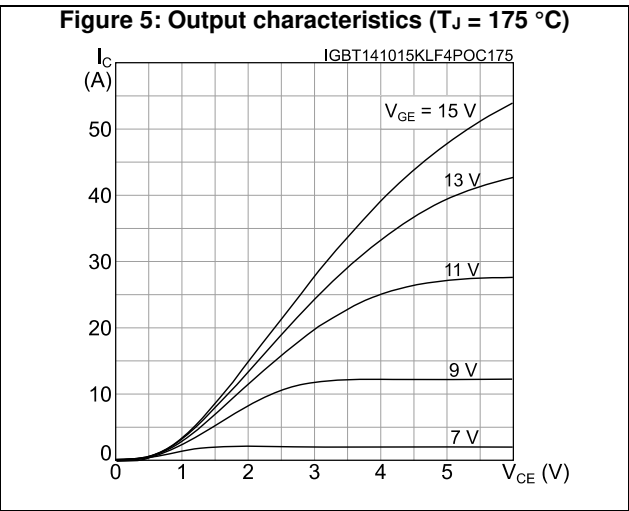
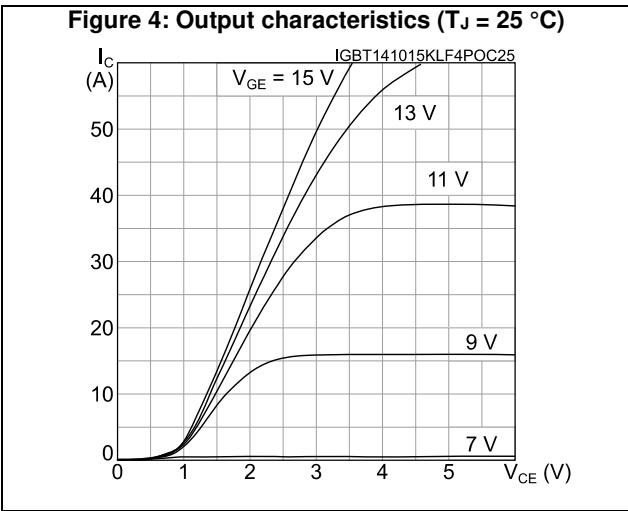
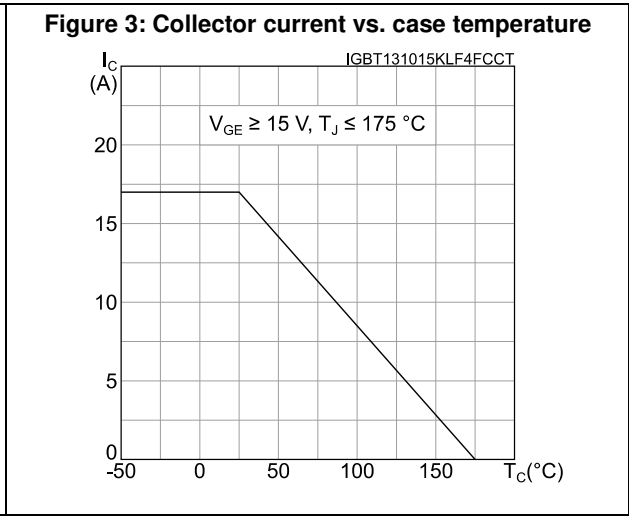
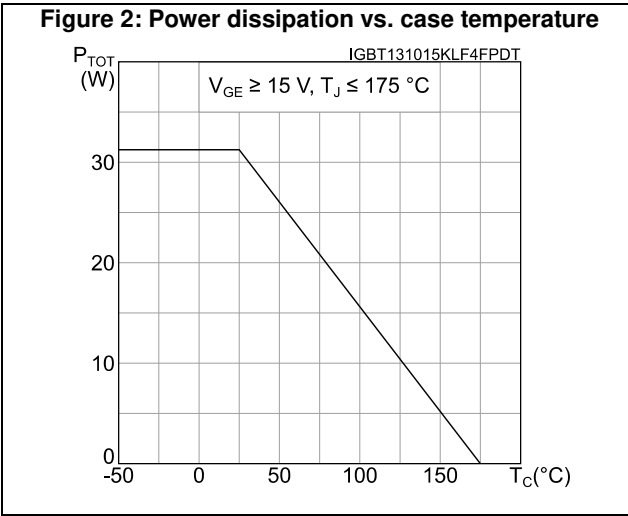


Figure 8: Collector current vs. switching frequency

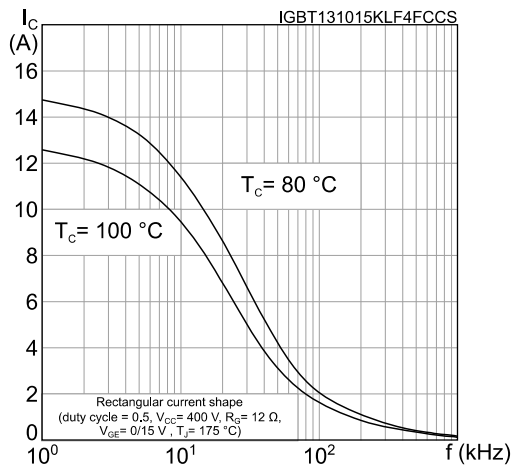


Figure 9: Forward bias safe operating area

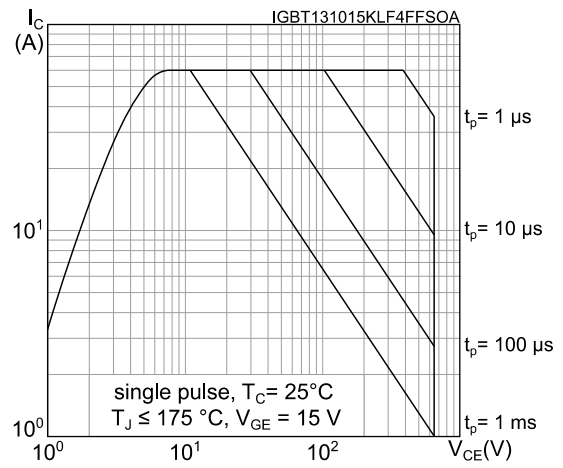


Figure 10: Transfer characteristics

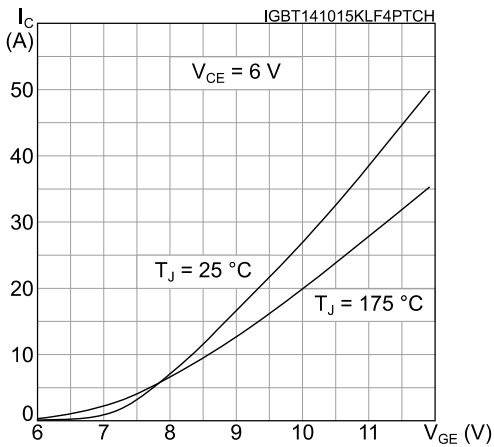


Figure 11: Diode VF vs. forward current

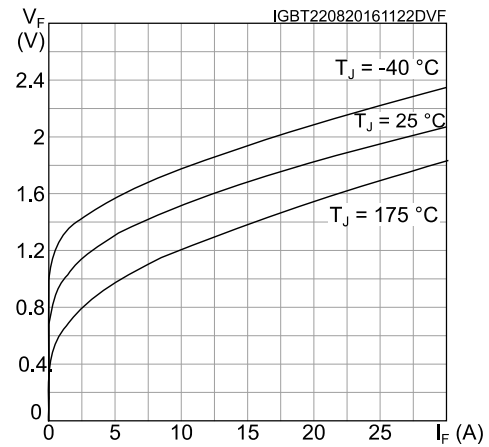


Figure 12: Normalized VGE(th) vs. junction temperature

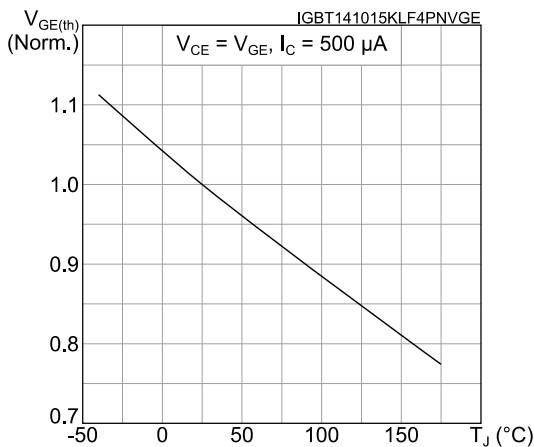
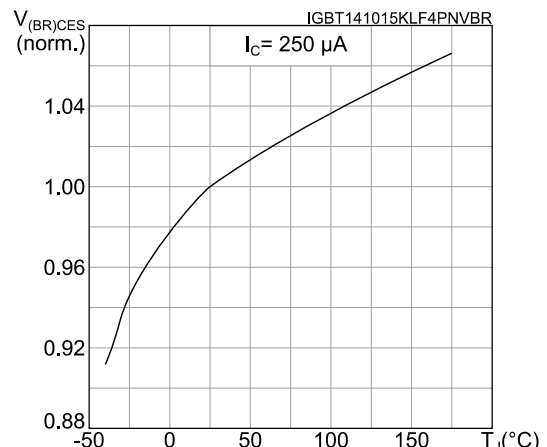
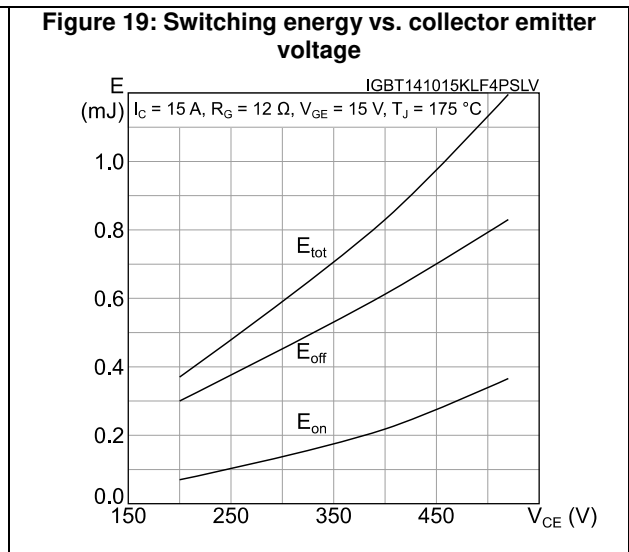
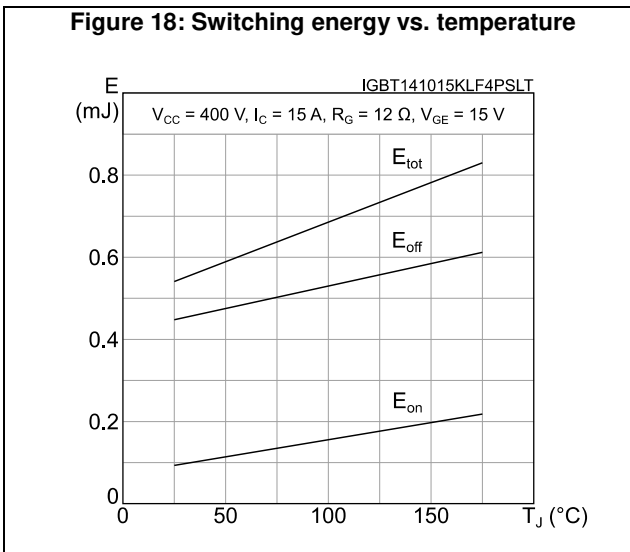
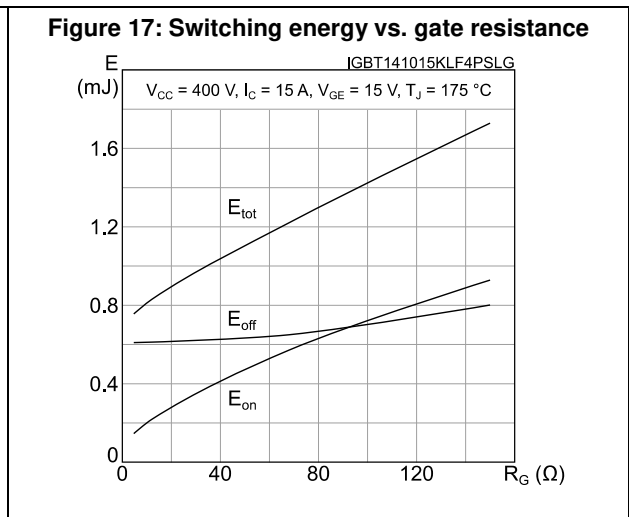
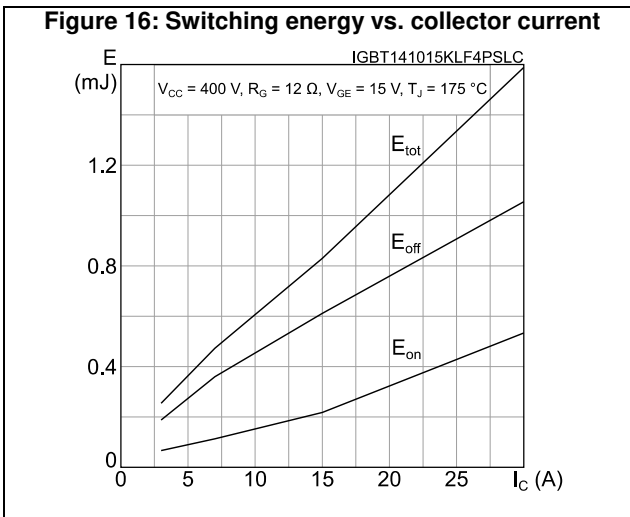
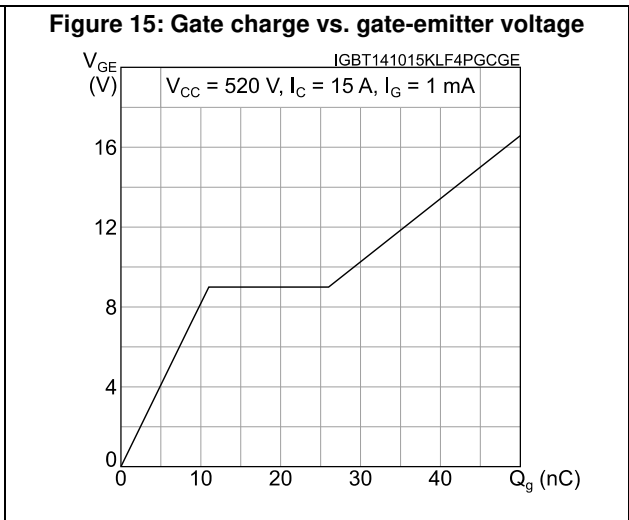
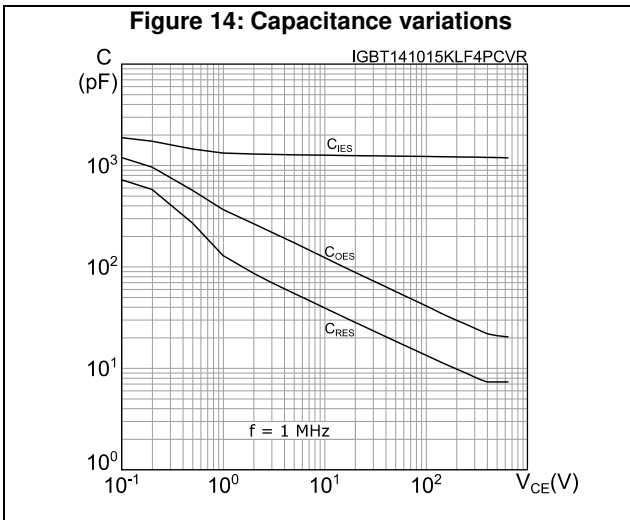


Figure 13: Normalized V(BR)CES vs. junction temperature





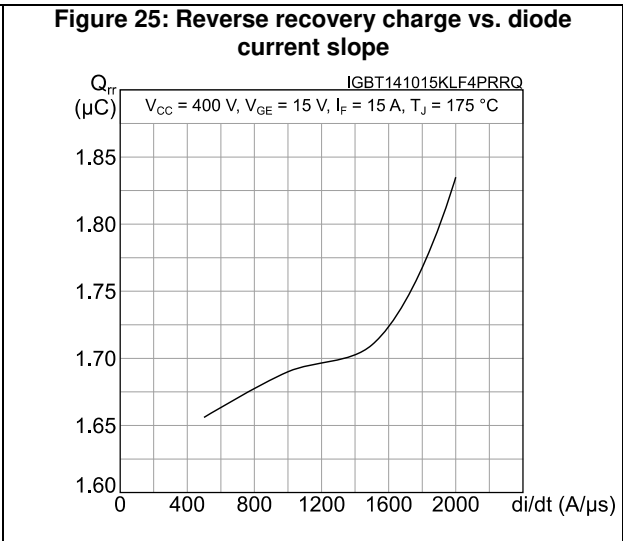
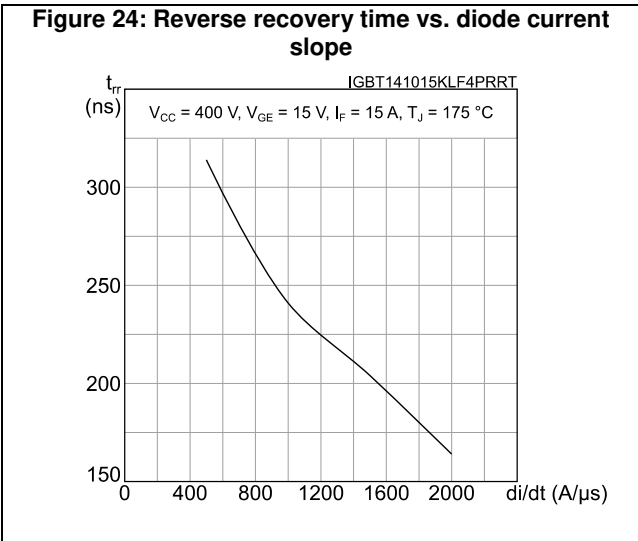
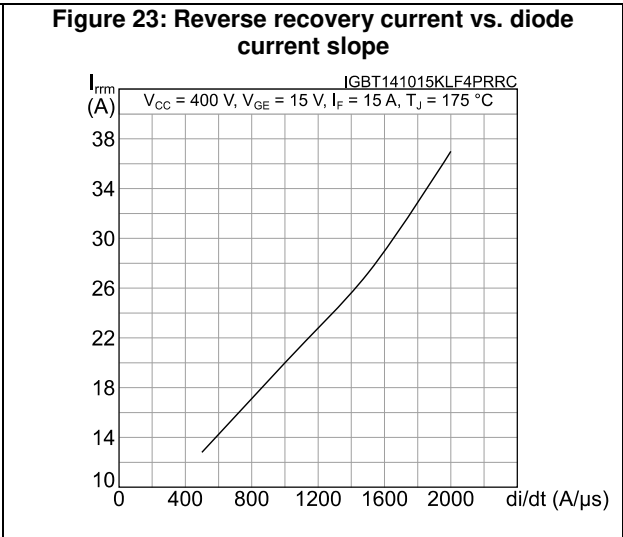
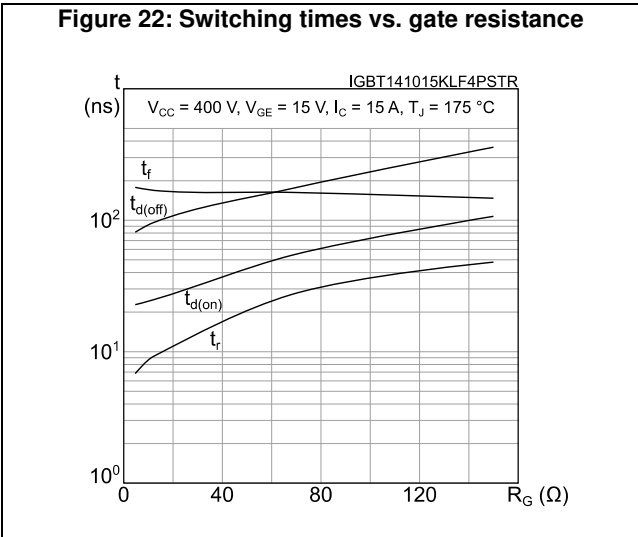
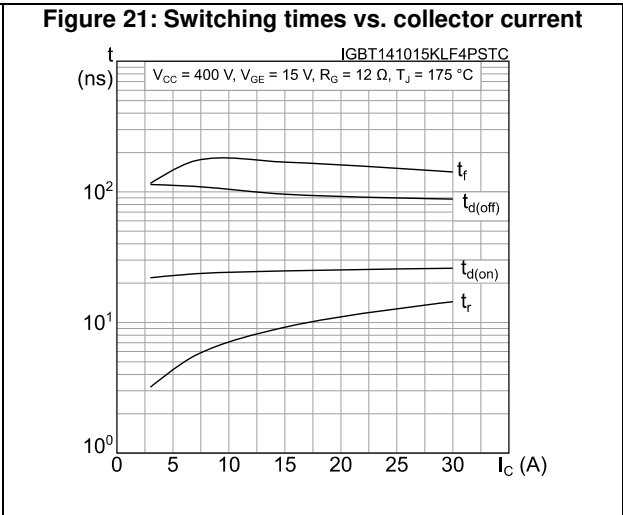
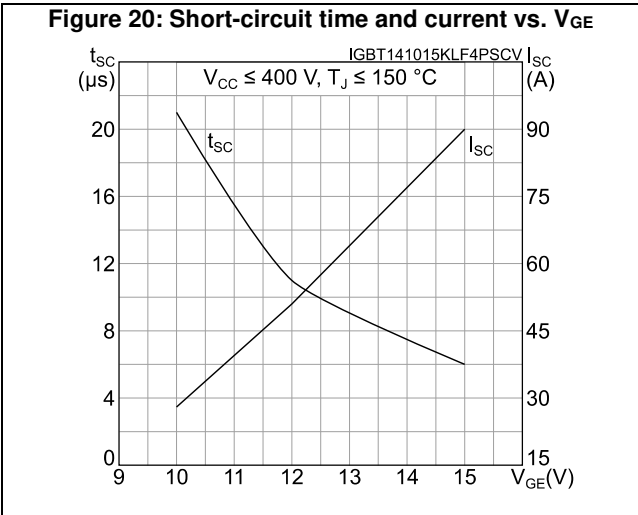


Figure 26: Reverse recovery energy vs. diode current slope

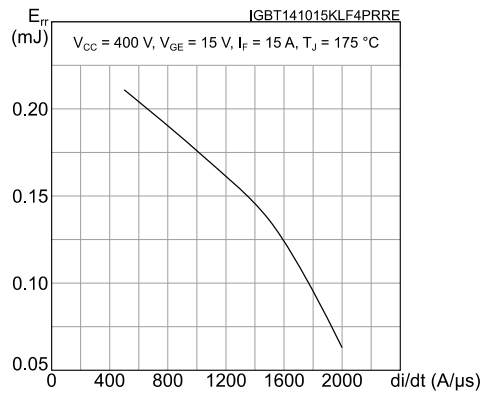
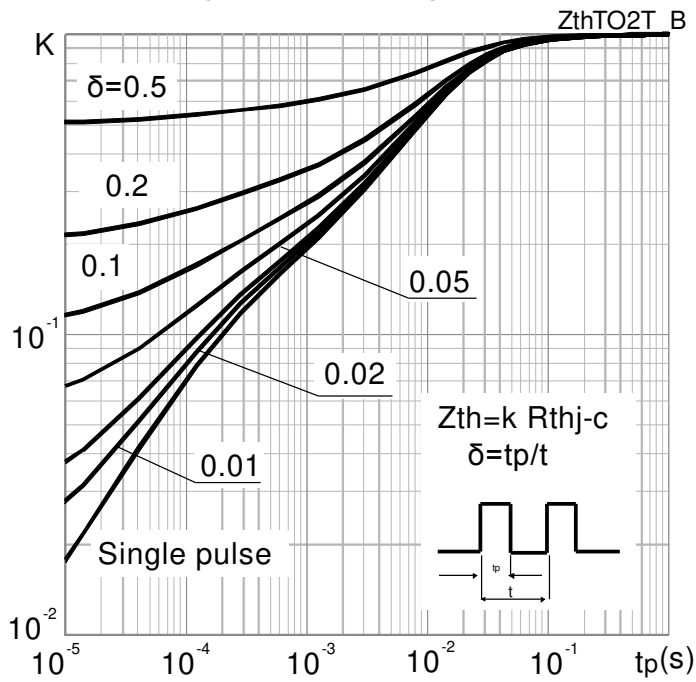
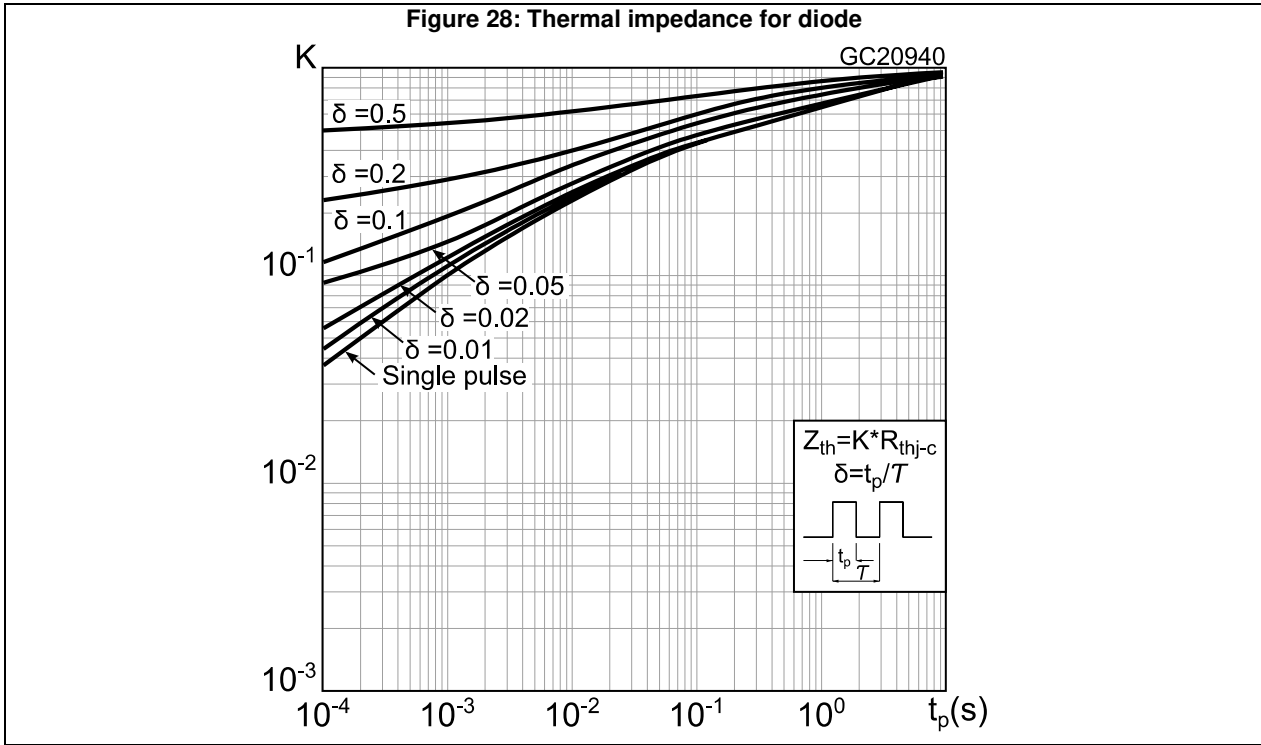


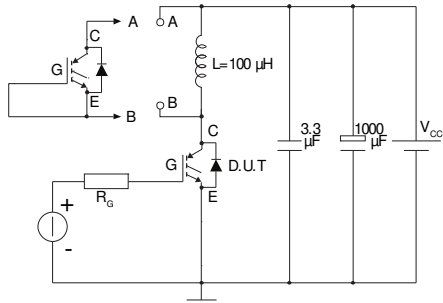
Figure 27: Thermal impedance for IGBT





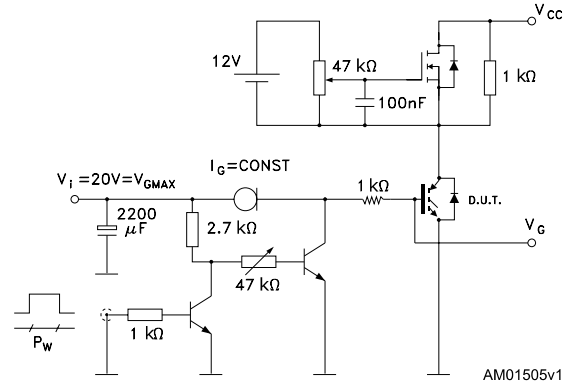
3 Test circuits

Figure 29: Test circuit for inductive load switching



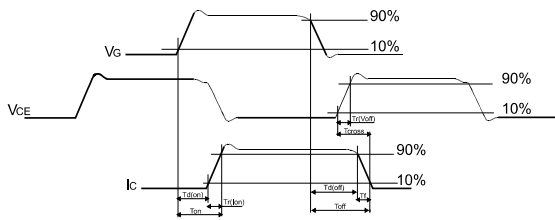
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Figure 30: Gate charge test circuit



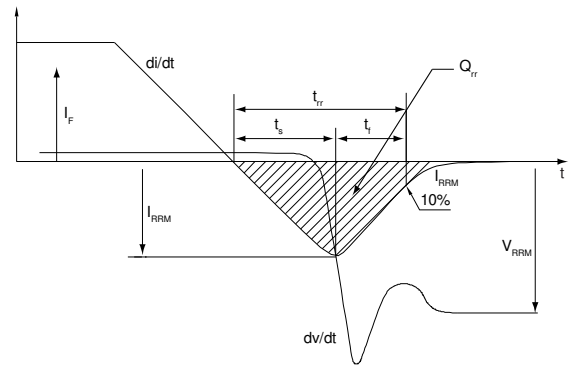
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Figure 31: Switching waveform



AM01506v1

Figure 32: Diode reverse recovery waveform



AM01507v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO-220FP package information

Figure 33: TO-220FP package outline

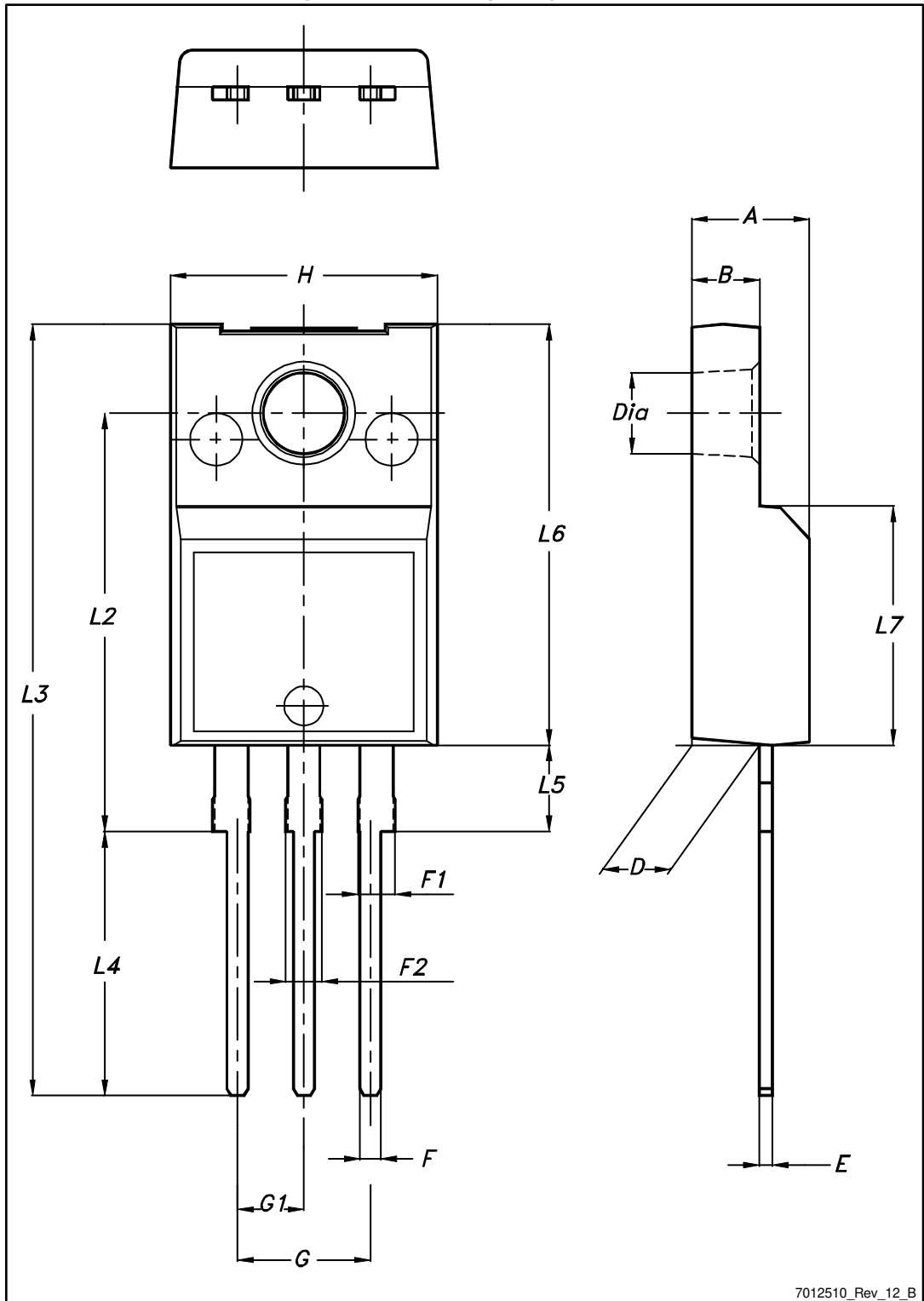


Table 8: TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

5 Revision history

Table 9: Document revision history

Date	Revision	Changes
14-Oct-2015	1	First release.
22-Aug-2016	2	Datasheet promoted from preliminary data to production data. Changed <i>Figure 11: "Diode VF vs. forward current"</i> . Updated: <i>Table 2: "Absolute maximum ratings"</i> and <i>Table 6: "IGBT switching characteristics (inductive load)"</i> . Updated: <i>Figure 16: "Switching energy vs. collector current"</i> , <i>Figure 17: "Switching energy vs. gate resistance"</i> , <i>Figure 18: "Switching energy vs. temperature"</i> and <i>Figure 19: "Switching energy vs. collector emitter voltage"</i> .
04-May-2017	3	Modified: title, features and applications on cover page. Modified <i>Table 4: "Static characteristics"</i> , <i>Table 5: "Dynamic characteristics"</i> , <i>Table 7: "Diode switching characteristics (inductive load)"</i> Updated <i>Section 4: "Package information"</i> . Minor text changes.

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